

**IN THE SPECIFICATION:**

**Please rewrite** the two new paragraphs that were added at the end of page 6 or top of page 7, by the Amendment filed July 12, 2005, so that they read as follows:

In Figs. 3(a)- 3(c), the line break on the right side indicates that region 6 may extend horizontally in the figures farther than is ~~shown, such that an area of the region 6 would be greater than an area of the region 4 and/or region 5. Even without taking the break into account, shown.~~ Fig. 3(c) shows that the area occupied by the etched non-doped polysilicon ~~region 6~~ dummy gate pattern is larger than the total area occupied by the N-type and P-type polysilicon ~~regions~~ gates which have been etched.

~~Figs. 3(a)- 3(c) also show how the regions are contiguous.~~